electrically conductive layer, and curing said formed spacer members after silk screening.

38. The method of claim 37 including forming said spacer members by silk screening said material on both of said first and second electrically conductive layers, and curing said formed spacer members.

39. The method of claim 37 wherein said curing includes subjecting said spacer members to ultraviolet light.

40. The method of claim 37 wherein said curing includes drying said spacer members at less than about 300 degrees C. for less than about 40 minutes.

41. The method of claim 35 wherein said forming includes substantially matching the index of refraction of said spacer members to the index of refraction of said one transparent, electrically conductive layer.

42. The method of claim 35 wherein said forming of said spacer members includes incorporating nanoscale particles as said inorganic material.

43. The method of claim 42 wherein said forming of said spacer members includes incorporating nano-particle metal oxides as said nanoscale particles.

44. The method of claim 42 wherein said forming of said spacer members includes incorporating a pig men t as said nanoscale particles.

45. The method of claim 35 including forming said spacer members to include at least one of a compound for surface modification of said inorganic material, and a cross-linking initiator.

46. The method of claim 35 including forming said spacer members from an organic-inorganic nano-composites.

47. The method of claim 35 wherein said forming includes preparing a paste of said material and silk screening said spacer members onto said one electrically conductive layer from said paste.

48. The method of claim 47 including silk screening said spacer members with a mesh screen such that at least one of said spacer members has a width dimension of at least about 15 microns.

49. The method of claim 48 including silk screening said spacer members with a mesh screen such that at least one of said spacer members has a height dimension of at least about 3 microns.

50. The method of claim 48 including silk screening said spacer members with a mesh screen such that at least one of said spacer members has a height dimension of about 3 microns to about 25 microns.

51. The method of claim 47 including silk screening said spacer members with a mesh screen such that at least one of said spacer members has a width dimension of about 15 microns to about 125 microns.

52. The method of claim 47 including silk screening said spacer members with a mesh screen such that at least one of said spacer members has a height dimension of at least about 3 microns.

53. The method of claim 47 including silk screening said spacer members with a mesh screen such that at least one of said spacer members has a height dimension of about 3 microns to about 25 microns.

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